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(54) Title: POST-DEPOSITION CLEANING METHODS AND FORMULATIONS FOR SUBSTRATES WITH CAP LAYERS

(57) Abstract: One embodiment of the present invention is a method of fabricating an integrated circuit. The method includes providing a substrate having a metal and dielectric damascene metallization layer and depositing substantially on the metal a cap. After deposition of the cap, the substrate is cleaned with a solution comprising an amine to provide a pH for the cleaning solution of 7 to about 13. Another embodiment of the presented invention is a method of cleaning substrates. Still another embodiment of the present invention is a formulation for a cleaning solution.

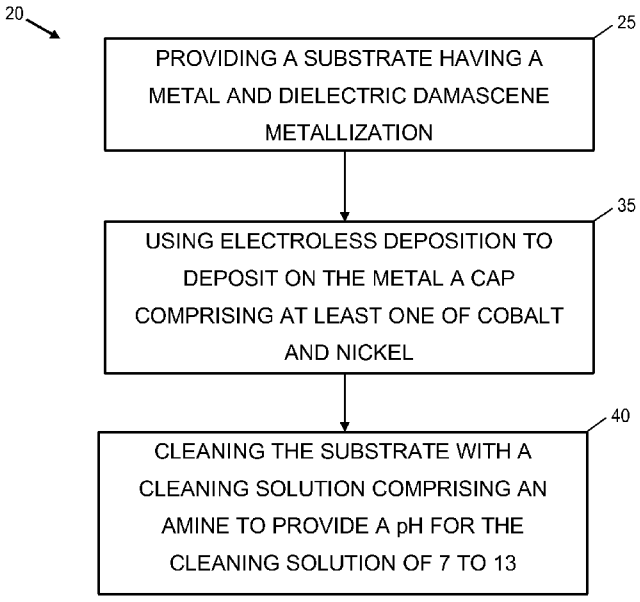


FIG. 1

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